Product data sheet

1. General description

NPN low VCEsat transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS5520X-Q

2. Features and benefits

- High h_{FE} and low V_{CEsat} at high current operation
- High collector current capability: I_C maximum 5 A
- · Higher efficiency leading to less heat generation
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Medium power peripheral drivers, e.g. fans and motors
- · Strobe flash units for DSC and mobile phones
- · Inverter applications, e.g. TFT displays
- · Power switch for LAN and ADSL systems
- Medium power DC-to-DC conversion
- Battery chargers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	20	V
I _C	collector current		-	-	5	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	10	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 5 A; I_B = 500 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	32	44	mΩ

5. Pinning information

Table 2. Pinning information

10010 211	mining initeri			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		
3	В	base	3 2 1	B — (
			SOT89	sym123



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6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4520X-Q	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4520X-Q	%1F

[1] % = placeholder for manufacturing site code

8. Limiting values

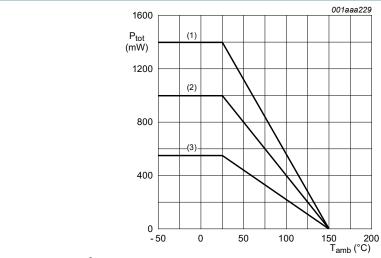
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	20	V
V_{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
Ic	collector current			-	5	А
I _{CRM}	repetitive peak collector current		[1] [2]	-	7	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	10	А
I _B	base current			-	1	А
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	2	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2] [3]	-	2.5	W
			[2]	-	0.55	W
			[4]	-	1	W
			[5]	-	1.4	W
			[6]	-	1.6	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] Operated under pulsed conditions: pulse width $t_p \le 10$ ms; duty cycle $\delta \le 0.2$.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [3] Operated under pulsed conditions: $t_p \le 10$ ms; $\delta \le 0.2$.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [6] Device mounted on a 7 cm² ceramic PCB, 1 cm² single-sided copper and tin-plated.

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- (1) FR4 PCB; 6 cm² mounting pad for collector (2) FR4 PCB; 1 cm² mounting pad for collector
- (3) FR4; standard footprint

Power derating curves Fig. 1.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from	in free air [1] [[1] [3] [4] [5]	[1] [2]	-	-	50	K/W
	junction to ambient		[1]	-	-	225	K/W
			[3]	-	-	125	K/W
			[4]	-	-	90	K/W
			[5]	-	-	80	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Operated under pulsed conditions: $t_p \le 10$ ms; $\delta \le 0.2$. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². [3]
- [4]
- Device mounted on a 7 cm² ceramic PCB, 1 cm² single-sided copper and tin-plated.

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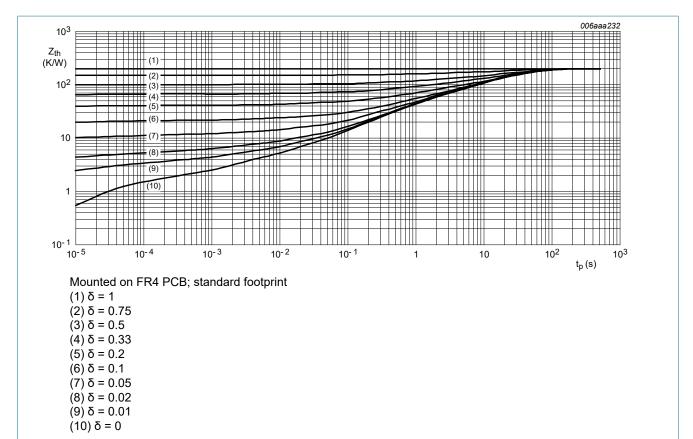
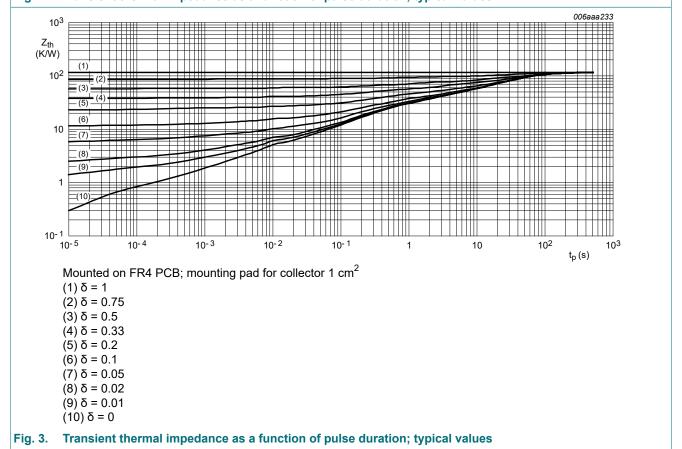
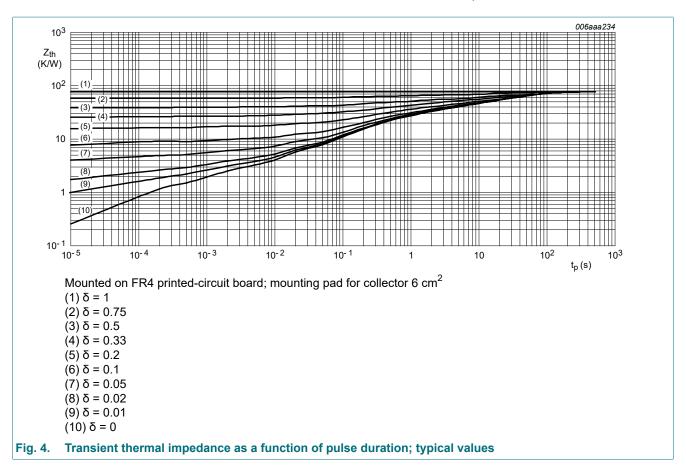


Fig. 2. Transient thermal impedance as a function of pulse duration; typical values



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Ісво	collector-base cut-off	V _{CB} = 20 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 20 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
ЕВО	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
CES	collector-emitter cut-off current	V _{CE} = 20 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
η _E	DC current gain	V _{CE} = 2 V; I _C = 0.5 A; T _{amb} = 25 °C	300	450	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	300	440	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; $\delta \le 0.02$; T_{amb} = 25 °C	250	420	-	
		V_{CE} = 2 V; I_{C} = 5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	200	380	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 0.5 A; I _B = 5 mA; T _{amb} = 25 °C	-	35	50	mV
		I _C = 1 A; I _B = 10 mA; T _{amb} = 25 °C	-	50	70	mV
		I_C = 2.5 A; I_B = 125 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	85	120	mV
		I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	130	180	mV
		I_C = 5 A; I_B = 500 mA; pulsed; $t_p \le$	-	160	220	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	32	44	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.9	1.05	V
		I_C = 5 A; I_B = 500 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.96	1.1	V
V_{BEon}	base-emitter turn-on voltage	V _{CE} = 2 V; I _C = 2 A; T _{amb} = 25 °C	-	0.74	0.85	V
ĪΤ	transition frequency	V_{CE} = 10 V; I_{C} = 100 mA; f = 100 MHz; T_{amb} = 25 °C	100	125	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	90	110	pF

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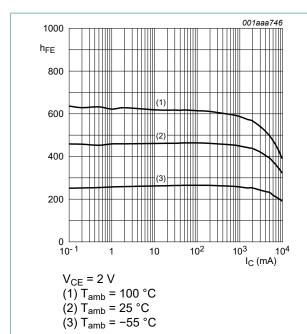


Fig. 5. DC current gain as a function of collector current; typical values

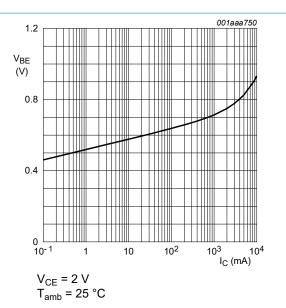


Fig. 6. Base-emitter voltage as a function of collector current; typical values

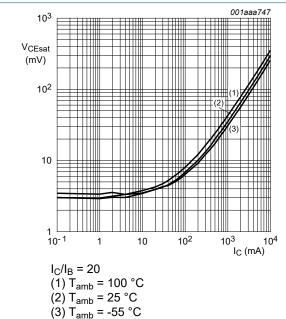
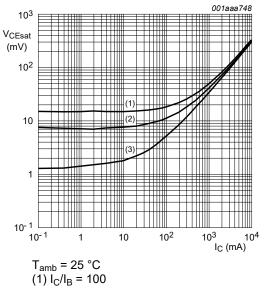


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



(2) $I_C/I_B = 50$ (3) $I_C/I_B = 10$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

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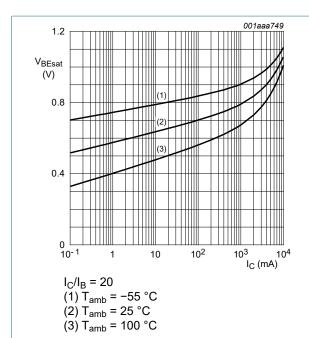
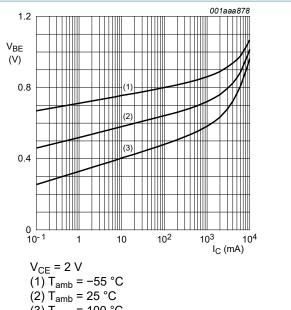
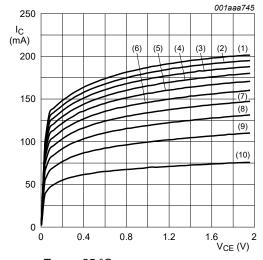


Fig. 9. collector current; typical values



(3) $T_{amb} = 100 \, ^{\circ}C$

Base-emitter saturation voltage as a function of Fig. 10. Base-emitter voltage as a function of collector current; typical values



T_{amb} = 25 °C

(1) $I_B = 5 \text{ mA}$

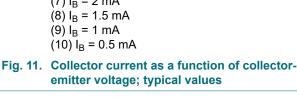
 $(2) I_B = 4.5 \text{ mA}$

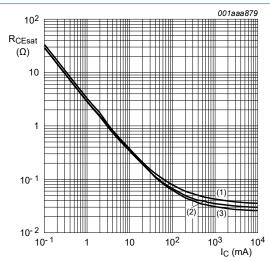
(3) $I_B = 4 \text{ mA}$

 $(4) I_B = 3.5 \text{ mA}$

(5) $I_B = 3 \text{ mA}$ (6) $I_B = 2.5 \text{ mA}$

(7) $I_B = 2 \text{ mA}$





 $I_{\rm C}/I_{\rm B} = 20$

(1) T_{amb} = 100 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 12. Equivalent on-resistance as a function of collector current; typical values

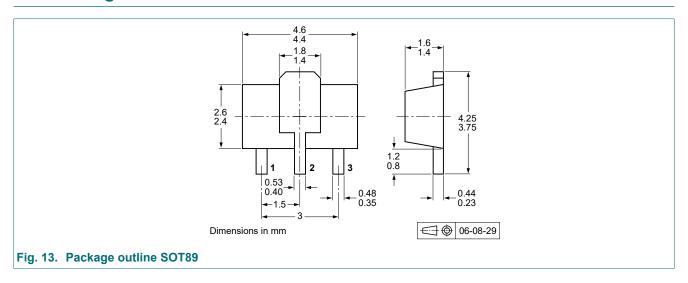
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11. Test information

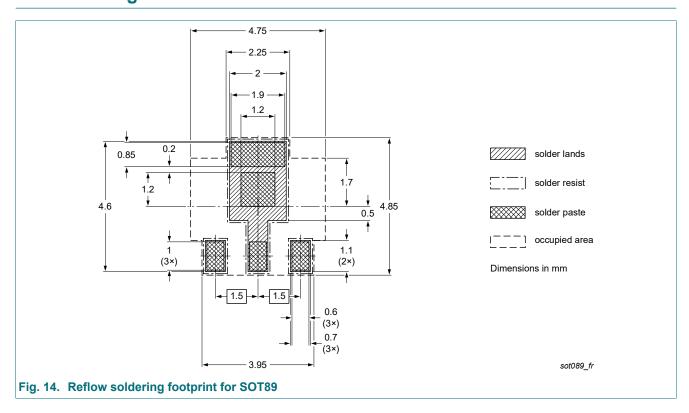
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

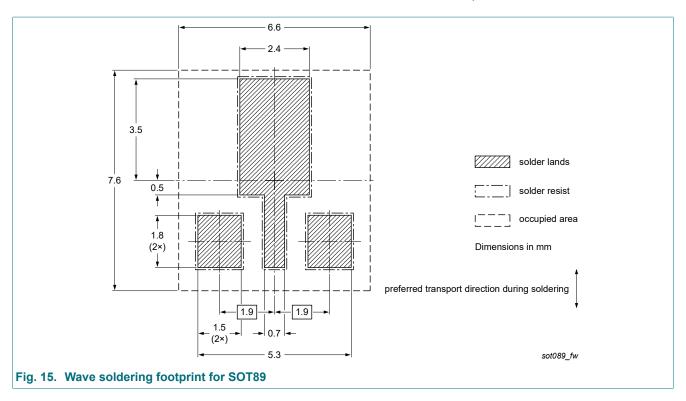
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4520X-Q v.1	20240119	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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	Features and benefits

For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 19 January 2024

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